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	Filing Date		2006-06-07	
	First Named Inventor	T. Fujii		
	Art Unit	2828		
	Examiner Name	Not yet assigned		
	Attorney Docket Number	G&C 30794.108USWO		

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1	BENISTY, H. et al., "Impact of Planar Microcavity Effects on Light Extraction-Part I: Basic Concepts and Analytical Trends," IEEE Journal of Quantum Electronics, 34(9), pp. 1612-1631 (1998)	<input type="checkbox"/>
2	BILLEB, A. et al., "Microcavity effects in GaN epitaxial films and in Ag/GaN/sapphire structures," Appl. Phys. Lett. 70 (21), pp. 2790-2792 (1997)	<input type="checkbox"/>
3	BORODITSKY, M. et al., "Light-Emitting Diode Extraction Efficiency," SPIE 3002, pp. 119-122 (1995)	<input type="checkbox"/>
4	CAO, X.A. et al., "Electrical effects of plasma damage in p-GaN," Appl. Phys. Lett. 75(17), pp. 2569-2571 (1999)	<input type="checkbox"/>
5	CHU, C.-F. et al., "Comparison of p-Side Down and p-Side Up GaN Light-Emitting Diodes Fabricated by Laser Lift-Off," Jpn. J. Appl. Phys. 42 (Part 2, No. 2B), pp. L147-L150 (2003)	<input type="checkbox"/>
6	DELBEKE, D. et al., "High-Efficiency Semiconductor Resonant-Cavity Light-Emitting Diodes: A Review," IEEE Journal on Selected Topics in Quantum Electronics, 8(2), pp. 189-206 (2002)	<input type="checkbox"/>
7	GUO, X. et al., "Photon Recycling Semiconductor Light Emitting Diode," IEEE, pp. 23.6.1-23.6.4 (1999)	<input type="checkbox"/>
8	HARLE, V. et al., "Advanced Technologies for high efficiency GaInN LEDs for solid state lighting," Proc. of SPIE 5187, pp. 34-40 (2004)	<input type="checkbox"/>
9	HUH, C. et al., "Improved light-output and electrical performance of InGaN-based light emitting diode by microroughening of the p-GaN surface," J. of Appl. Phys. 93(11), pp. 9383-9385 (2003)	<input type="checkbox"/>
10	KAWAKAMI, Y. et al., "Dimensionality of Excitons in InGaN-Based Light Emitting Diodes," Phys. Stat. Sol. (a) 178, 331, pp. 331-336 (2000)	<input type="checkbox"/>
11	MINSKY, M.S. et al., "Room-temperature photoenhanced wet etching of GaN," Appl. Phys. Lett. 68(11), pp. 1531-1533 (1996)	<input type="checkbox"/>

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12	OHBA, Y. et al., "A study on strong memory effects for Mg doping in GaN metalorganic chemical vapor deposition," J. of Crystal Growth 145, pp. 214-218 (1994)	<input type="checkbox"/>
13	NISHIDA, T. et al., "Efficient and high-power AlGaIn-based ultraviolet light-emitting diode grown on bulk GaN," Appl. Phys. Lett. 79(6), pp. 711-712 (2001)	<input type="checkbox"/>
14	SCHNITZER, I. et al., "30% external quantum efficiency from surface textured, thin-film light-emitting diodes," Appl. Phys. Lett. 63(16), pp. 2174-2176 (1993)	<input type="checkbox"/>

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☐ See attached certification statement.

☐ Fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

☒ None

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A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/George H. Gates/	Date (YYYY-MM-DD)	2007-07-31
Name/Print	George H. Gates	Registration Number	33,500

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